



- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

CST4801 Product Summary

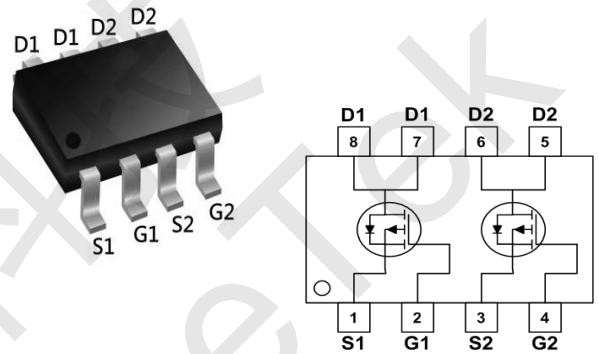
BVDSS	RDSON	ID
-30V	42mΩ	-6A

CST4801 Description

The CST4801 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST4801 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

CST4801 SOP8 Pin Configuration



CST4801 Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ C$	Continuous Drain Current	-6	A
$I_D@T_A=70^\circ C$	Continuous Drain Current	-3.6	A
I_{DM}	Pulsed Drain Current ²	-16	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.4	W
$P_D@T_A=70^\circ C$	Total Power Dissipation ³	0.9	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

CST4801 Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	105	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	---	$^\circ C/W$



CST4801 Dual P-Ch 30V Fast Switching MOSFETs

CST4801 Electrical Characteristics (T_J=25°C unless otherwise noted)

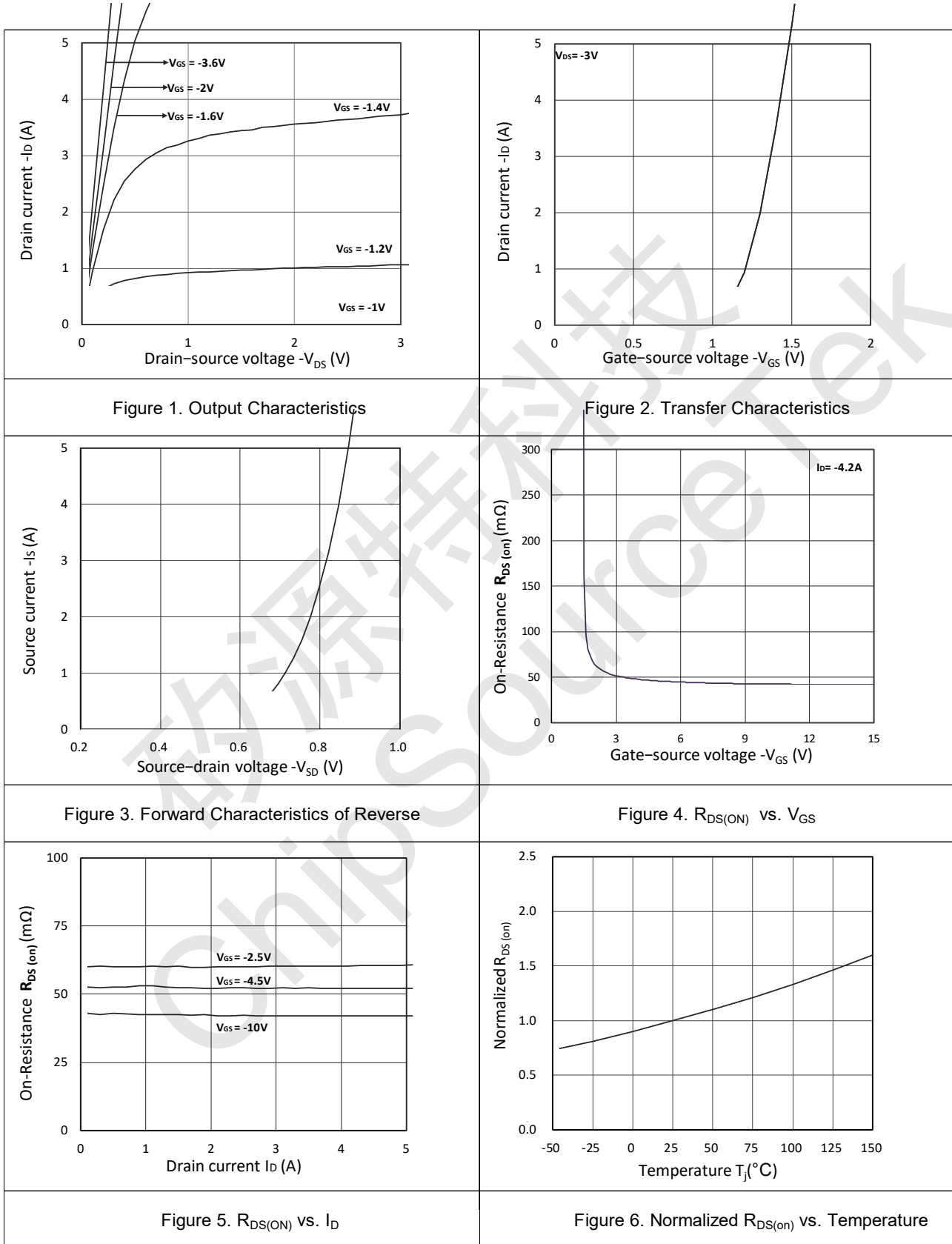
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±12V	-	-	±100	nA
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.7	-1	-1.3	V
Drain-Source on-Resistance ³	R _{DS(on)}	V _{GS} = -10V, I _D = -4.2A	-	42	60	mΩ
		V _{GS} = -4.5V, I _D = -4A	-	52	75	
		V _{GS} = -2.5V, I _D = -1A	-	60	90	
Dynamic Characteristics⁴						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz	-	745	-	pF
Output Capacitance	C _{oss}		-	70	-	
Reverse Transfer Capacitance	C _{rss}		-	57	-	
Switching Characteristics⁴						
Total Gate Charge	Q _g	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -4.2A	-	8	-	nC
Gate-Source Charge	Q _{gs}		-	1.8	-	
Gate-Drain Charge	Q _{gd}		-	2.7	-	
Turn-on Delay Time	t _{d(on)}	V _{GS} = -10V, V _{DD} = -15V, I _D = -4.2A, R _{GEN} = 6Ω	-	7	-	ns
Rise Time	t _r		-	3	-	
Turn-off Delay Time	t _{d(off)}		-	30	-	
Fall Time	t _f		-	12	-	
Drain-Source Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	I _S = -4.2A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	I _S		-	-	-Ĉ	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C
2. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.



CST4801 Typical Characteristics





CST4801 Dual P-Ch 30V Fast Switching MOSFETs

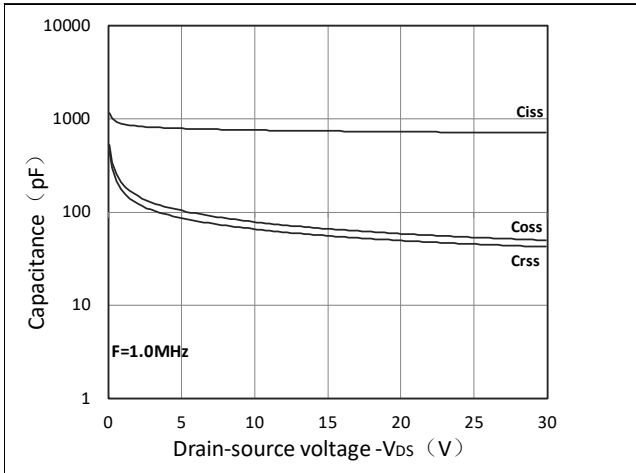


Figure 7. Capacitance Characteristics

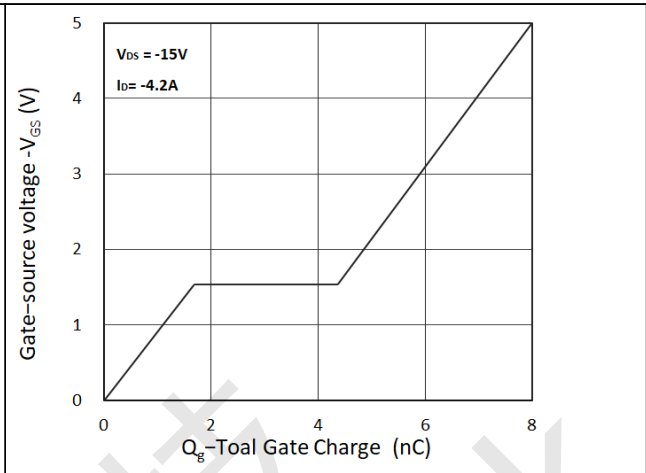


Figure 8. Gate Charge Characteristics

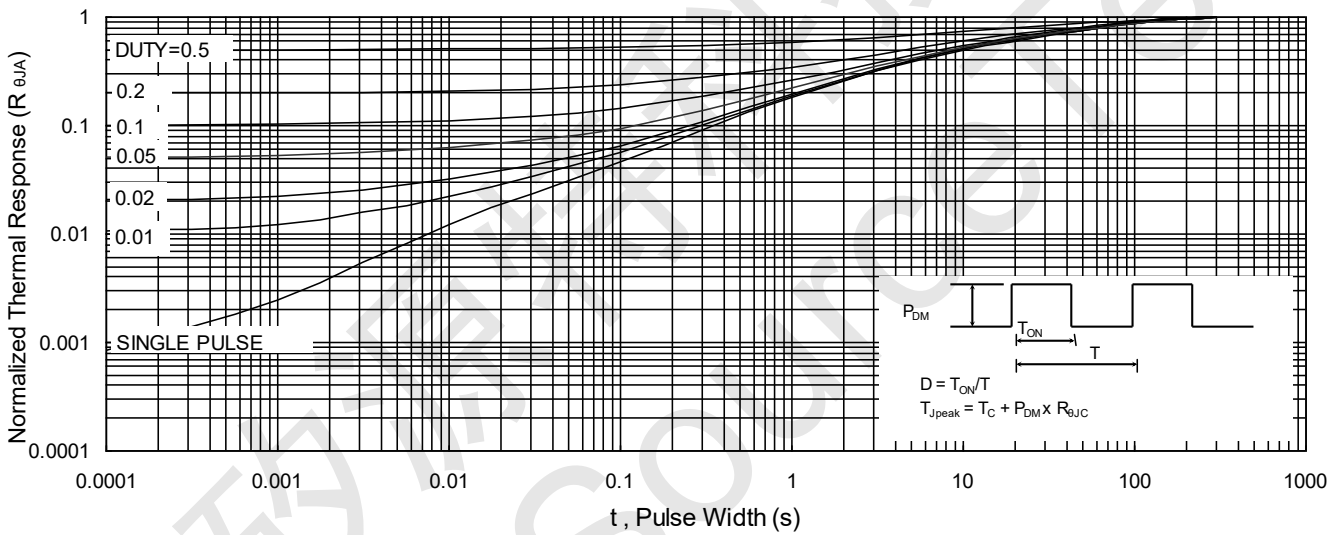


Fig.9 Normalized Maximum Transient Thermal Impedance

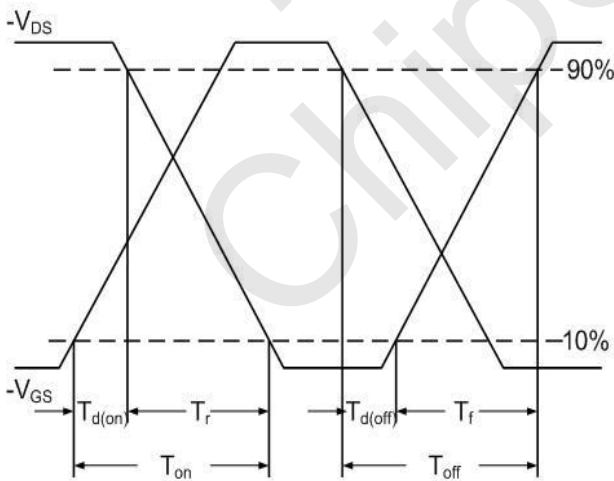


Fig.10 Switching Time Waveform

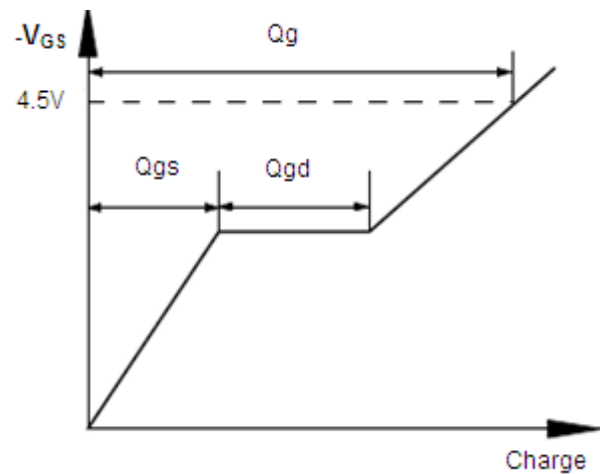


Fig.11 Gate Charge Waveform



CST4801 Package Mechanical Data- SOP-8

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°